

# 2SH14

## Silicon N-Channel IGBT

# HITACHI

1st. Editon  
Feb. 1995

### Application

High speed power switching

### Features

- High speed switching
- Low on saturation voltage

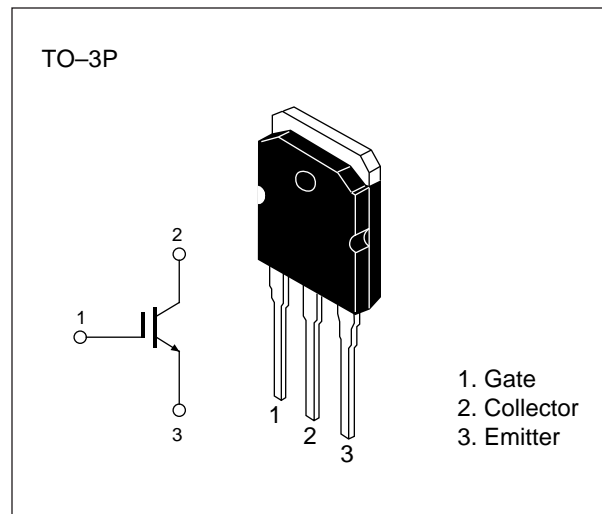


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	$V_{CES}$	600	V
Gate to emitter voltage	$V_{GES}$	$\pm 20$	V
Collector current	$I_C$	30	A
Collector peak current	$i_{c(peak)}$	60	A
Collector dissipation	$P_C^*$	100	W
Channel temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

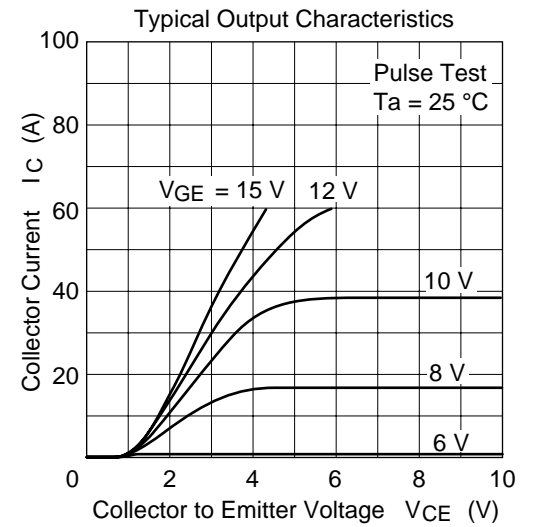
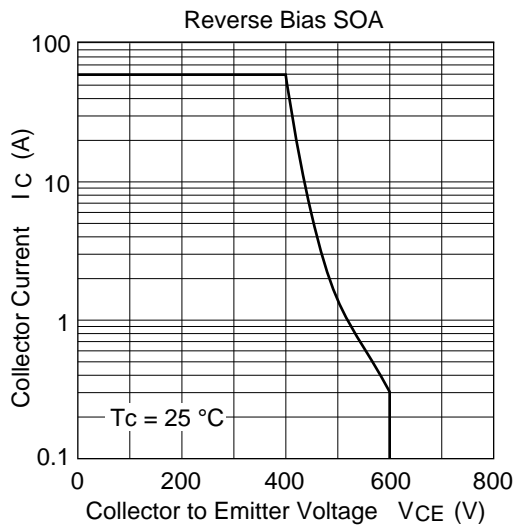
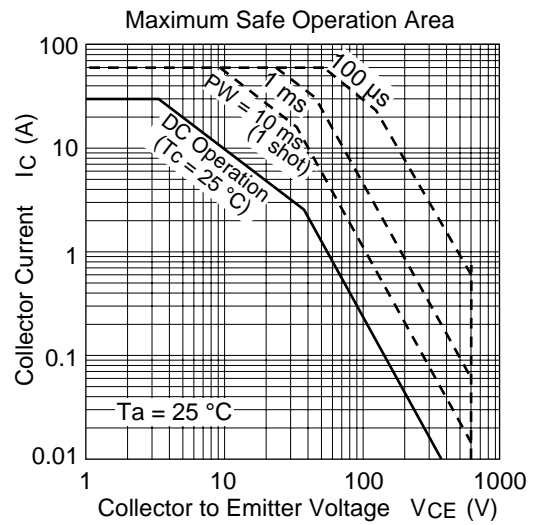
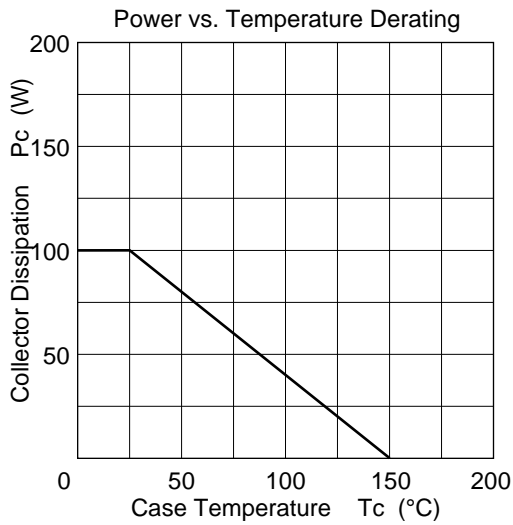
\* Value at  $T_c = 25^\circ\text{C}$

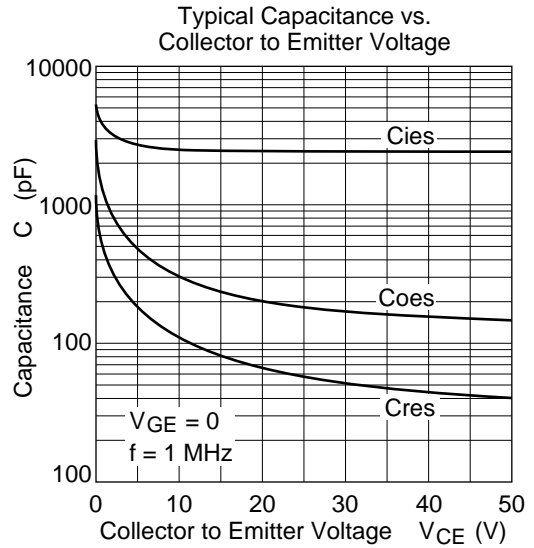
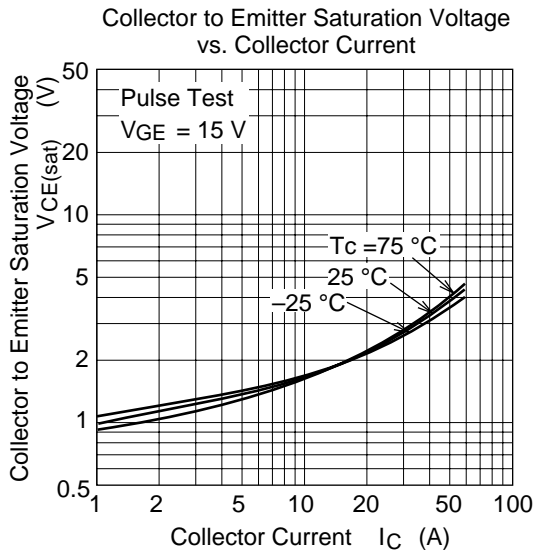
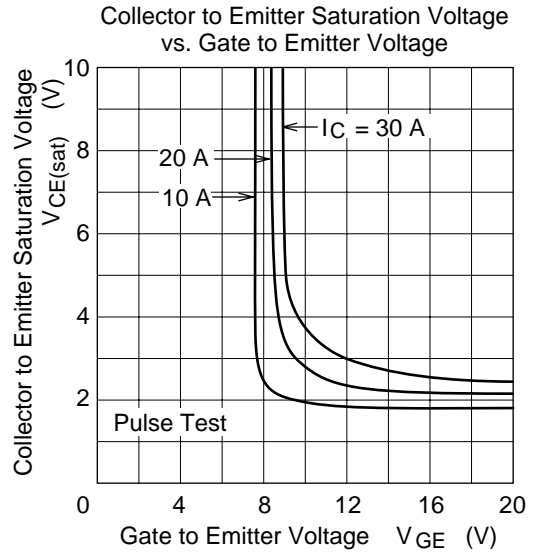
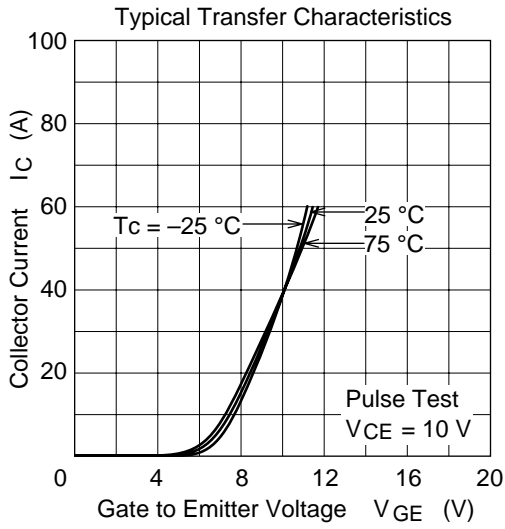
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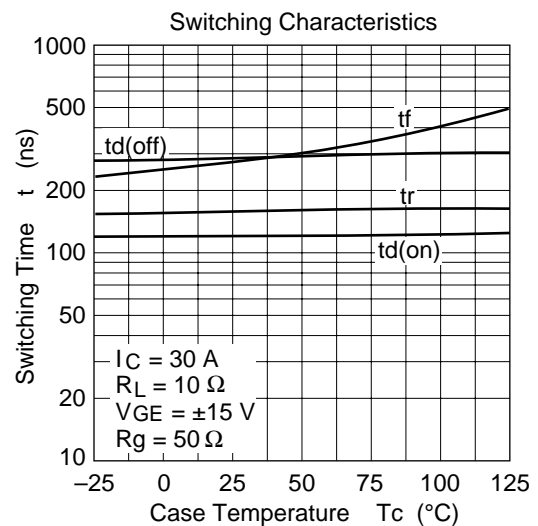
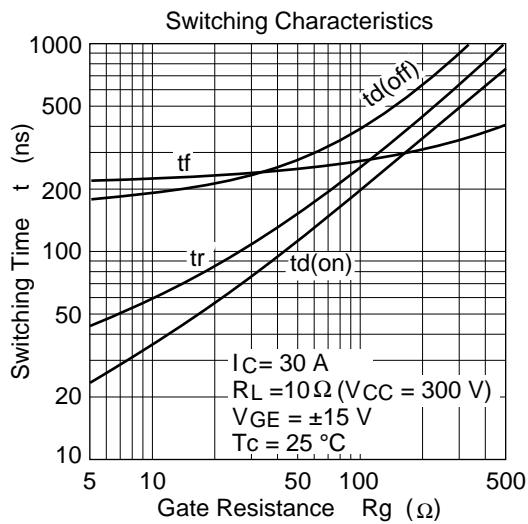
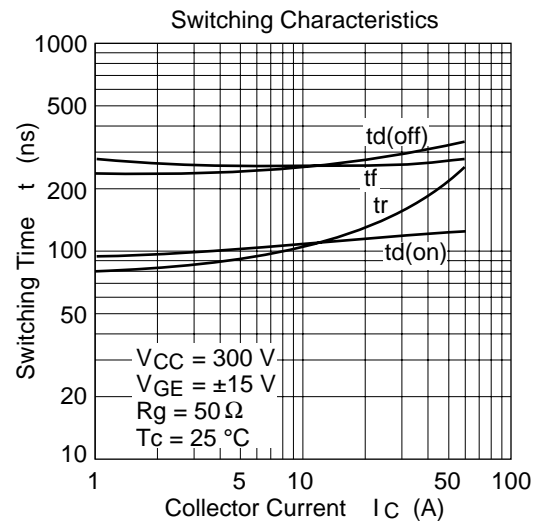
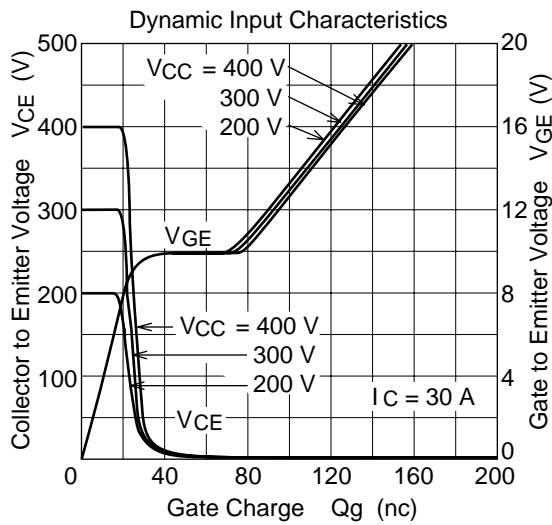
**Table 2 Electrical Characteristics (Ta = 25°C)**

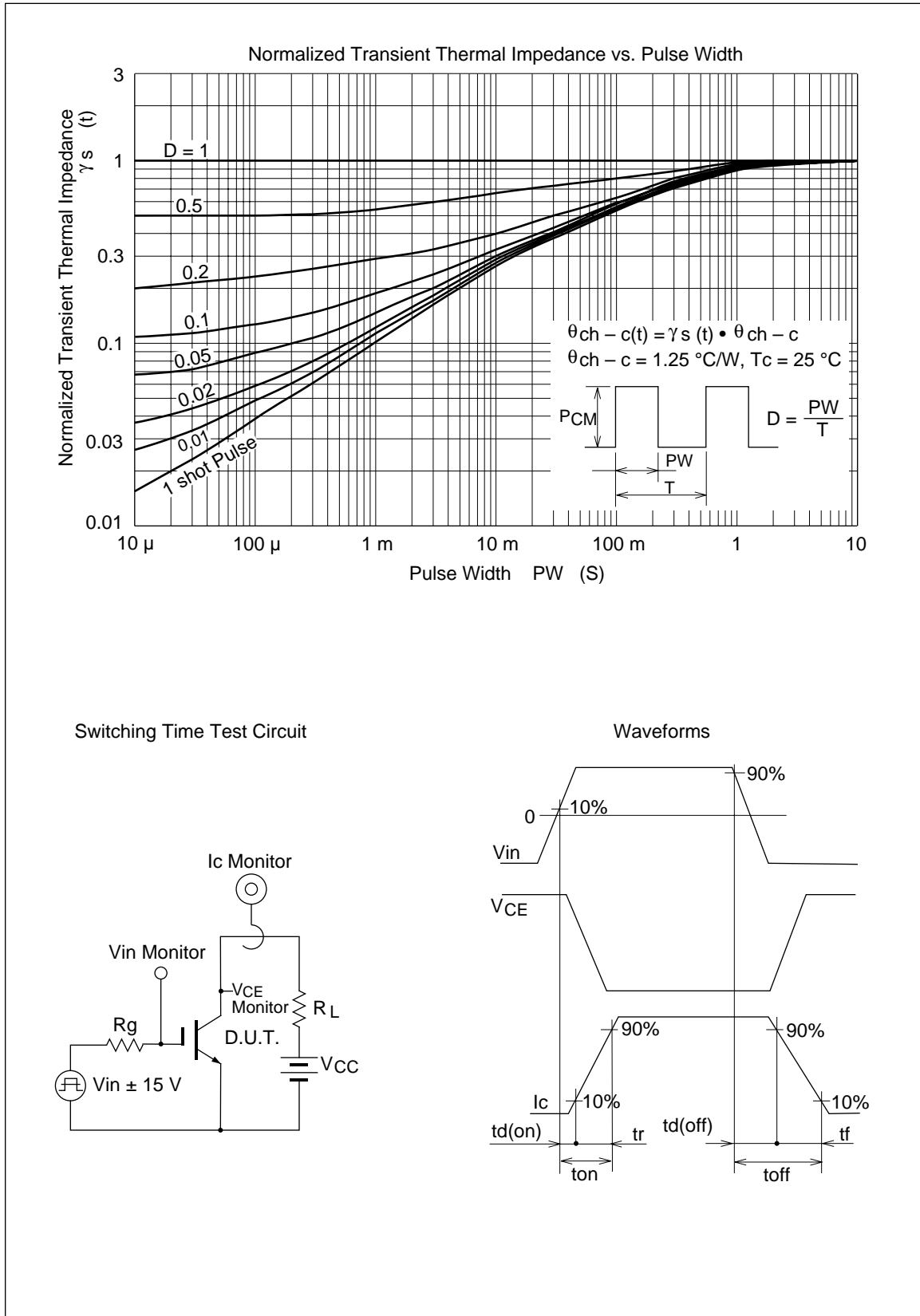
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CES}$	600	—	—	V	$I_C = 100 \mu A, V_{GE} = 0$
Zero gate voltage collector current	$I_{CES}$	—	—	0.5	mA	$V_{CE} = 600 V, V_{GE} = 0$
Gate to emitter leak current	$I_{GES}$	—	—	$\pm 1$	$\mu A$	$V_{GE} = \pm 20 V, V_{CE} = 0$
Gate to emitter cutoff current	$V_{GE(off)}$	3.0	—	5.0	V	$I_C = 1 mA, V_{CE} = 10 V$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	2.0	—	V	$I_C = 15 A, V_{GE} = 15 V$
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	2.6	3.3**	V	$I_C = 30 A, V_{GE} = 15 V$
Input capacitance	$C_{ies}$	—	2600	—	pF	$V_{CE} = 10 V, V_{GE} = 0, f = 1 MHz$
Switching time	$t_r$	—	160	—	ns	$I_C = 30 A,$ $R_L = 10 \Omega,$ $V_{GE} = \pm 15 V$ $R_g = 50 \Omega$
	$t_{on}$	—	300	—		
	$t_f$	—	300	600		
	$t_{off}$	—	600	1200		

\*\* $V_{CE(sat)2}$  is specified at the correlated test condition ( $I_C=20A$ )



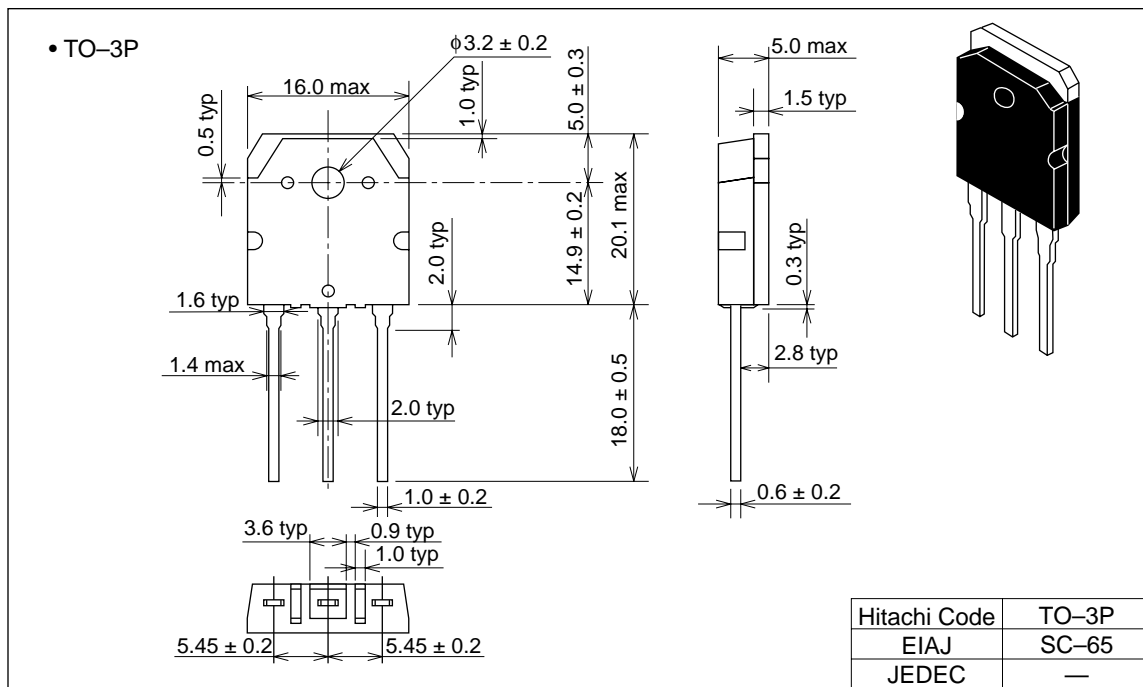






Package Dimensions

Unit : mm



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## Hitachi, Ltd.

Semiconductor & Integrated Circuits.  
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL      NorthAmerica      : <http://semiconductor.hitachi.com/>  
             Europe                : <http://www.hitachi-eu.com/hel/ecg>  
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## For further information write to:

Hitachi Semiconductor  
(America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1> (408) 433-0223

Hitachi Europe GmbH  
Electronic components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX

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